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The invention relates to semiconductor technology and can be used, in particular, in devices for converting solar radiation into electrical energy.

The method for p<sup>+</sup>InP-p<sup>-</sup>InP-n<sup>+</sup>CdS structure growth for photovoltaic cells consists in that the p<sup>-</sup>InP layer is grown on a substrate, made in the form of a p<sup>+</sup>InP plate with crystallographic orientation (100), misorientation of 3...5° in the direction (110) and charge carrier concentration of 10<sup>18</sup> cm<sup>-3</sup>, is deposited on the frontal part of the plate by the quasi-closed volume method a n<sup>+</sup>CdS layer, is deposited on the reverse side of the plate an ohmic contact of Ag+5%Zn, is thermally treated at a temperature of 450°C, is deposited the ohmic contact of In onto the n<sup>+</sup>CdS layer, is thermally treated at a temperature of 250°C, and is deposited by the electron beam evaporation method, at a temperature of 300°C, a SiO<sub>2</sub> antireflection layer.

Claims: 1